IFW

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s):	En-Hsing Chen, et al.		
Title:	NAND MEMORY ARRAY INCORPORATING MULTIPLE SERIES SELECTION DEVICES AND METHOD FOR OPERATION OF SAME		
Application No.:	10/729,865	Filed:	December 5, 2003
Examiner:	Nguyen, Van Thu T.	Group Art Unit:	2824
Atty. Docket No.:	023-0029	Confirmation No.:	8494

March 15, 2005

Mail Stop Amendment
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INFORMATION DISCLOSURE STATEMENT
37 C.F.R. § 1.97(b)

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, § 1.97 and § 1.98, the undersigned brings to the Examiner's attention in the above-identified application the patents, publications, applications or other information identified in the attached:

- ☒ Form(s) PTO/SB/08A (5 page(s), with copy of 4 reference(s)).
- ☒ Form(s) PTO/SB/08B (2 page(s), with copy of 20 reference(s)).
- ☒ Listing of Pending Applications (1 page(s), with copy of no application(s)).
- ☐ Other: N/A

Citation of such information shall not be construed as (i) an admission that the information necessarily is, or corresponds to, prior art with respect to the instant invention, (ii) a representation that a search has been made, other than as described herein, or (iii) an admission that the information cited herein is, or is considered to be, material to patentability as defined in § 1.56(b).

For each item of information listed that is not in the English language, the undersigned has provided a concise explanation of the relevance through (i) an English language abstract, (ii) an English language equivalent application, or (iii) if cited in a search report or other action by a foreign patent office in a counterpart foreign application, an English language version of the search report or action that indicates the degree of relevance found by the foreign office.

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☐ Certain information was submitted to, or cited by, the Office in Application No(s). N/A, filed N/A, to which the above-identified application claims priority under 35 U.S.C. § 120. In accordance with 37 C.F.R. § 1.98(d), copies of that information are not included.

☒ Pursuant to 1287 OG 163 (October 19, 2004), for those cited pending U.S. patent applications filed (or which entered the national stage under 35 U.S.C. § 371) on or after June 30, 2003 or which are otherwise stored in the USPTO's Image File Wrapper system, copies are not included.

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☐ This Information Disclosure Statement is filed within three months of the filing date of a national application other than a continued prosecution application under § 1.53(d) or within three months of entry of the national stage as set forth in § 1.491 in an international application. Therefore, no fee is required.

☒ The undersigned believes that this Information Disclosure Statement is being filed before the mailing date of a first Office action on the merits or before the mailing date of a first Office action after the filing of a request for continued examination under § 1.114. Therefore, no fee is believed required.

If however, this Information Disclosure Statement is filed after the period specified in § 1.97(b), the undersigned hereby authorizes the Commissioner to charge the fee set forth in § 1.17(p) to Deposit Account No. 50-0631.

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Andrew C. Graham — Date: 3-15-05

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Respectfully submitted,

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PTO/SB/08A (Substitute for form 1449/PTO)	**Attorney Docket No.:** *023-0029*
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT	**First Named Inventor:** *En-Hsing Chen et al.*
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	Examiner Name: *Van Thu Nguyen*
Sheet 1 of 5	**Date Submitted:** *March 15, 2005*

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	AN	JA 62-142363	06-25-1987			
	AO	JA 62-155568	07-10-1987			
	AP	JA-2001-358237	12-26-2001			
	AQ	JA-2002-280467	09-27-2002			
Examiner Signature		**Examiner Signature**			**Date Considered**	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	BG					
	BH					
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	BW					
	BX					
	BY					
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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
	AA	DURISETY, CHANDRA SEKHAR ACHARYULU, "Analysis and Characterization of Single-Poly Floating Gate Devices in 0.35um PDSOI Process", A Thesis Presented for the Master of Science Degree, The University of Tennessee, Knoxville, December 2002, pp. i-viii and 1-80.	
	AB	EVANS, ROBERT J., ET AL., "Energy Consumption Modeling and Optimization for SRAM's," IEEE Journal of Solid-State Circuits, Vol. 30, No. 5, May 1995, pp. 571-579.	
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	AJ	LIN, HORNG-CHIH, ET AL., "Ambipolar Schottky-Barrier TFTs," IEEE Transactions on Electron Devices, Vol. 49, No. 2, February 2002, pp. 264-270.	
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	AP	STURM, J. C., ET AL., "Leakage Current Modeling of Series-Connected Thin Film Transistors," IEEE Transactions on Electron Devices, Vol. 42, No. 8, August 1995, pp. 1561-1563.	
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	AU		
	AV		
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